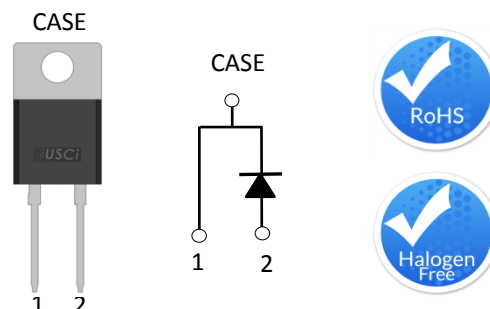


Description

United Silicon Carbide, Inc. offers the xR series of high performance SiC Schottky diodes. With zero reverse recovery charge and 175°C maximum junction temperature, USCi's diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



Part Number	Package	Marking
UJ2D1205T	TO-220-2L	UJ2D1205T

Features

- ♦ Positive temperature coefficient for safe operation and ease of paralleling
- ♦ 175°C maximum operating junction temperature
- ♦ Extremely fast switching not dependent on temperature
- ♦ Essentially no reverse or forward recovery
- ♦ RoHS compliant

Typical Applications

- ♦ Power converters
- ♦ Industrial motor drives
- ♦ Switching-mode power supplies
- ♦ Power factor correction modules

Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
DC blocking voltage	V_R		1200	V
Repetitive peak reverse voltage, $T_J=25^\circ\text{C}$	V_{RRM}		1200	V
Surge peak reverse voltage	V_{RSM}		1200	V
Maximum DC forward current	I_F	$T_C = 151^\circ\text{C}$	5	A
Non-repetitive forward surge current sine halfwave	I_{FSM}	$T_C = 25^\circ\text{C}$, $t_p = 10\text{ms}$	37.5	A
		$T_C = 110^\circ\text{C}$, $t_p = 10\text{ms}$	30	
Repetitive forward surge current sine halfwave, $D=0.1$	I_{FRM}	$T_C = 25^\circ\text{C}$, $t_p = 10\text{ms}$	21.3	A
		$T_C = 110^\circ\text{C}$, $t_p = 10\text{ms}$	13	
Non-repetitive avalanche energy	E_{AS}	$T_J = 25^\circ\text{C}$, $L = 10\text{mH}$, $I_{pk}=2.9\text{A}$, $V_{DD}=100\text{V}$	44	mJ
Power dissipation	P_{Tot}	$T_C = 25^\circ\text{C}$	93	W
		$T_C = 151^\circ\text{C}$	15	
Maximum junction temperature	$T_{J,max}$		175	$^\circ\text{C}$
Operating and storage temperature	T_J , T_{STG}		-55 to 175	$^\circ\text{C}$
Soldering temperatures, wavesoldering only allowed at leads	T_{sold}	1.6mm from case for 10s	260	$^\circ\text{C}$

Electrical Characteristics

$T_J = +25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Forward voltage	V_F	$I_F = 5\text{A}, T_J = 25^\circ\text{C}$	-	1.5	1.7	V
		$I_F = 5\text{A}, T_J = 175^\circ\text{C}$	-	2.5	3	
Reverse current	I_R	$V_R = 1200\text{V}, T_J = 25^\circ\text{C}$	-	30	190	μA
		$V_R = 1200\text{V}, T_J = 175^\circ\text{C}$	-	60	600	
Total capacitive charge ⁽¹⁾	Q_C	$V_R = 800\text{V}$		26		nC
Total capacitance	C	$V_R = 1\text{V}, f = 1\text{MHz}$		260		pF
		$V_R = 400\text{V}, f = 1\text{MHz}$		24		
		$V_R = 800\text{V}, f = 1\text{MHz}$		19		
Capacitance stored energy	E_C	$V_R = 800\text{V}$		6.8		μJ

(1) See Figure 8, Q_C is independent on T_J , di_F/dt , and I_F as shown in the application note USCi_AN0011.

Thermal characteristics

Parameter	symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Thermal resistance	$R_{\theta JC}$			1.19	1.6	$^\circ\text{C}/\text{W}$

Typical Performance

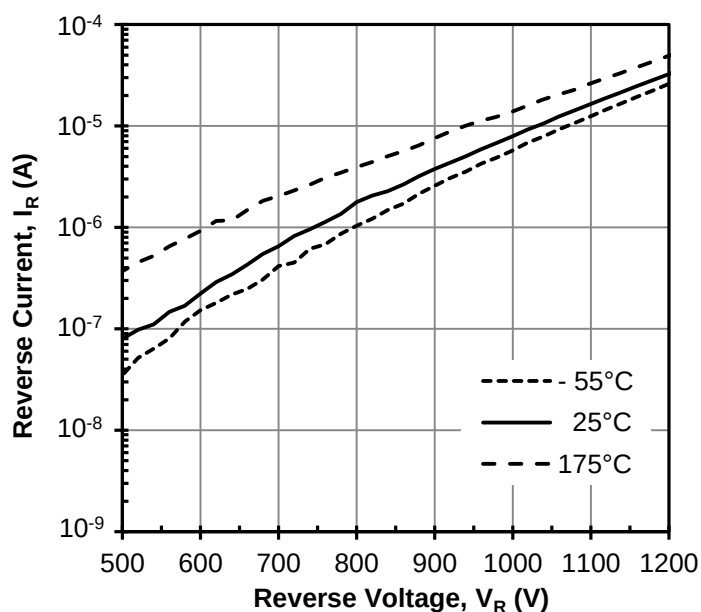


Figure 1 Typical reverse characteristics

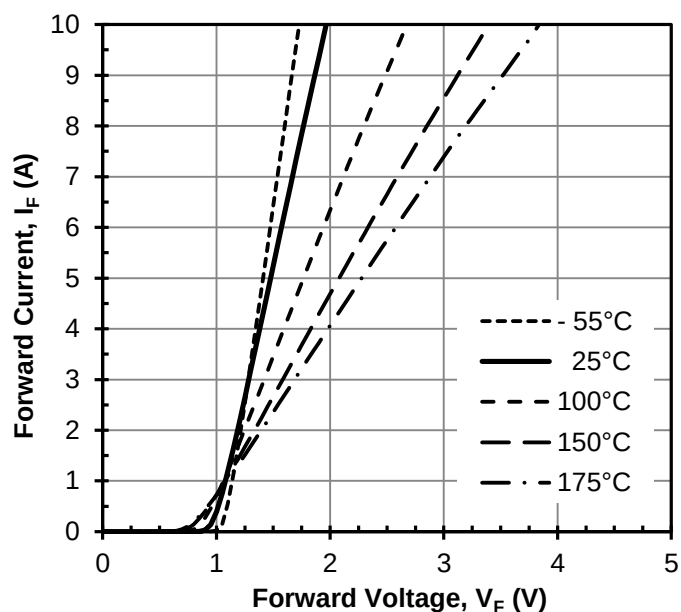


Figure 2 Typical forward characteristics

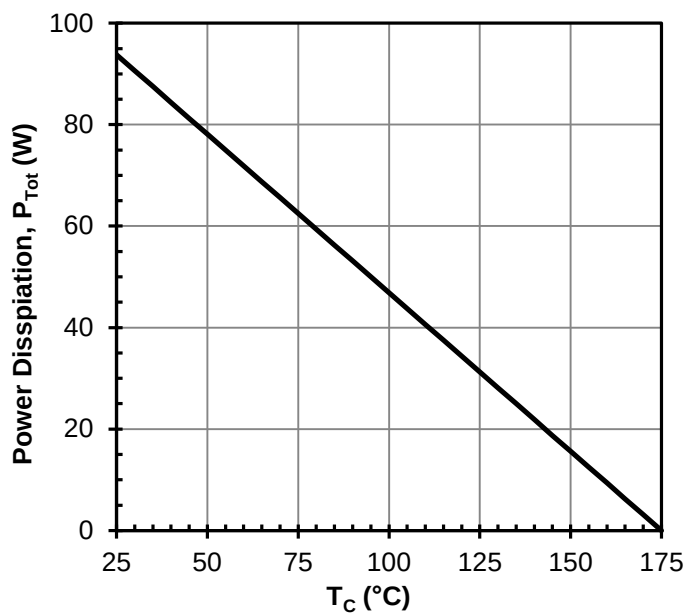


Figure 3 Power dissipation

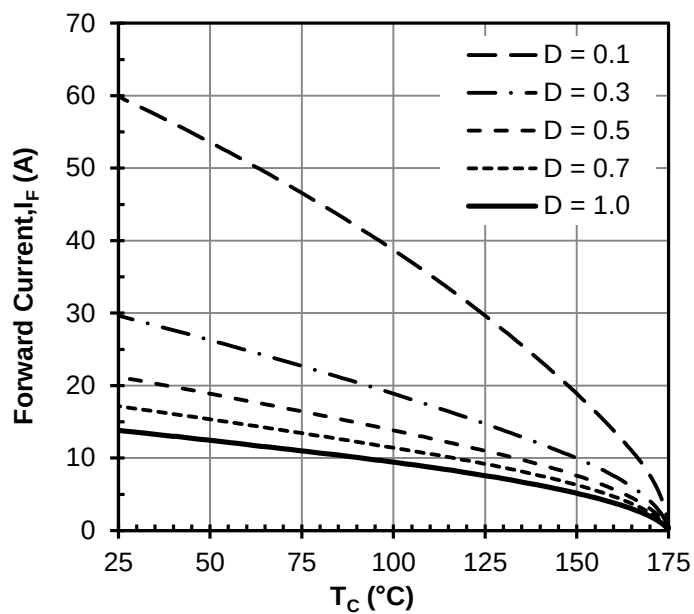


Figure 4 Diode forward current

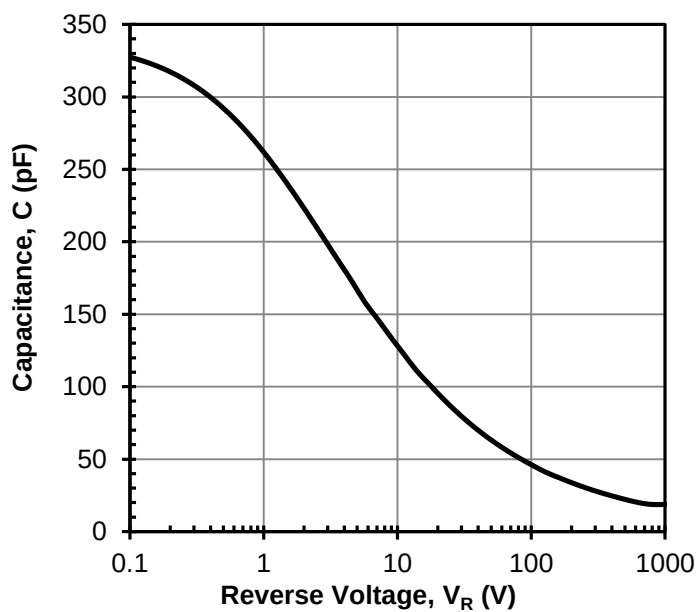


Figure 5 Capacitance vs. reverse voltage

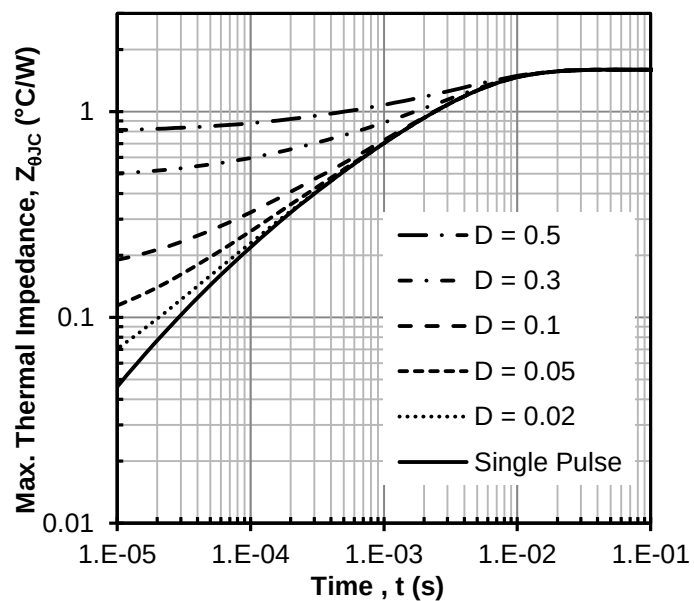


Figure 6 Maximum transient thermal impedance

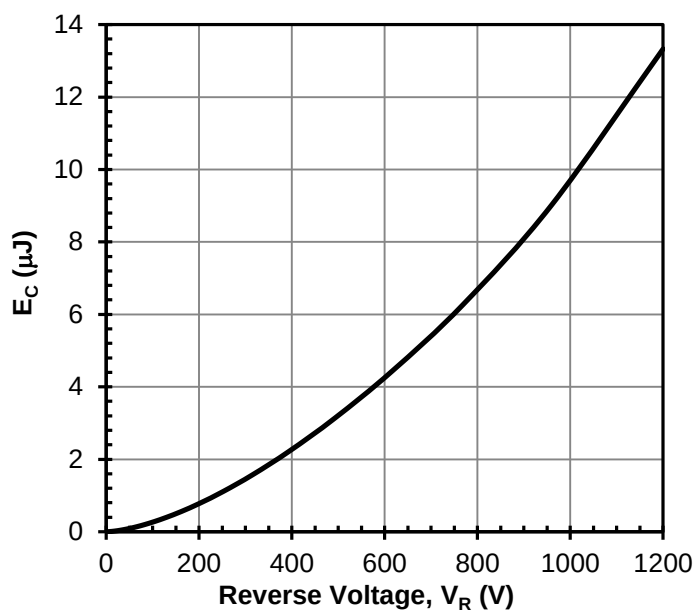


Figure 7 Typical capacitance stored energy vs. reverse voltage

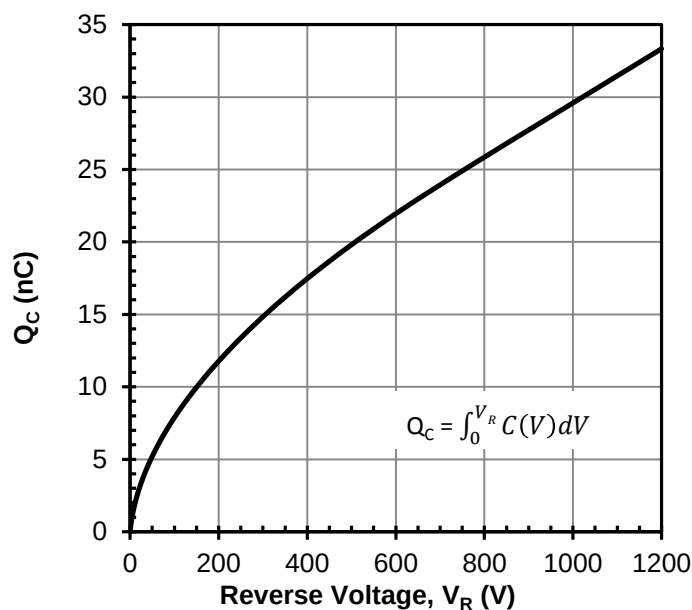


Figure 8 Typical capacitive charge vs. reverse voltage

Disclaimer

United Silicon Carbide, Inc. reserves the right to change or modify any of the products and their inherent physical and technical specifications without prior notice. United Silicon Carbide, Inc. assumes no responsibility or liability for any errors or inaccuracies within.

Information on all products and contained herein is intended for description only. No license, express or implied, to any intellectual property rights is granted within this document.

United Silicon Carbide, Inc. assumes no liability whatsoever relating to the choice, selection or use of the United Silicon Carbide, Inc. products and services described herein.